TetraFET

D2218UK



ROHS COMPLIANT METAL GATE RF SILICON FET

GOLD METALLISED

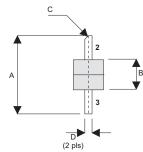
MULTI-PURPOSE SILICON

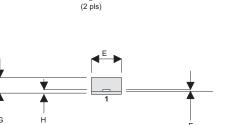
DMOS RF FET

20W - 12.5V - 500MHz

SINGLE ENDED

MECHANICAL DATA





DP

PIN 1 SOURCE PIN 2 DRAIN

PIN 3

GATE

DIM	mm	Tol.	Inches	Tol.
Α	16.51	0.25	0.650	0.010
В	6.35	0.13	0.250	0.005
С	45°	5°	45°	5°
D	1.52	0.13	0.060	0.005
Е	6.35	0.13	0.250	0.005
F	0.13	0.03	0.005	0.001
G	3.56	0.51	0.140	0.020
Н	0.64	0.13	0.024	0.005

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 10 dB MINIMUM

APPLICATIONS

 VHF/UHF COMMUNICATIONS from DC to 1 GHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

PD	Power Dissipation	70W
BV _{DSS}	Drain – Source Breakdown Voltage	40V
BV _{GSS}	Gate – Source Breakdown Voltage	±20V
I _{D(sat)}	Drain Current	16A
T _{stg}	Storage Temperature	–65 to 150°C
T _j	Maximum Operating Junction Temperature	200°C

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test C	Min.	Тур.	Max.	Unit	
B\/	Drain-Source	V _{GS} = 0	I _D = 10mA	40			V
BV _{DSS}	Breakdown Voltage	VGS = 0	D = 1000	40			v
	Zero Gate Voltage	\/ _ 12 5\/				0	m۸
IDSS	Drain Current	$V_{\rm DS} = 12.5V \qquad V_{\rm GS} = 0$				8	mA
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	$V_{DS} = 0$			8	μA
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA	$V_{DS} = V_{GS}$	0.5		7	V
9 _{fs}	Forward Transconductance*	V _{DS} = 10V	I _D = 1.6A	1.44			S
G _{PS}	Common Source Power Gain	P _O = 20W		10			dB
η	Drain Efficiency	V _{DS} = 12.5V	I _{DQ} = 1.6A	40			%
VSWR	Load Mismatch Tolerance	f = 500MHz		20:1			—
C _{iss}	Input Capacitance	V _{DS} = 12.5V V ₀	GS = -5V f = 1MHz			96	pF
C _{oss}	Output Capacitance	V _{DS} = 12.5V V ₀	GS = 0 f = 1MHz			80	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 12.5V V ₀	GS = 0 f = 1MHz			8	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

HAZARDOUS MATERIAL WARNING

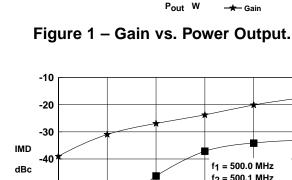
The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 2.5°C / W
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Vds = 12.5V

Idq = 1.6A

f =500MHz

10

15

5

14

12

10

8

6

4

2

0

0

Gain dB

20

25

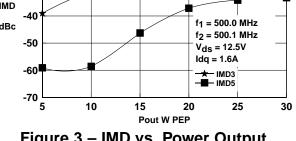


Figure 3 – IMD vs. Power Output.

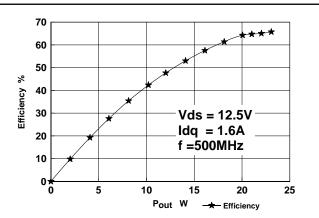
Typical S Parameters

$V_{DS} = 12.5V, I_{DQ} = 0.8A$! # MHZ S MA R 50

!Freq MHz 100 200	S11 mag 0.82 0.88	ang -160 -169	S21 mag 9.92 3.92	ang 72 50	S12 mag 0.018 0.011	ang -12 -16	S22 mag 0.7 0.81	ang -155 -162
300	0.91	-175	2.29	40	0.006	11	0.87	-169
400	0.93	-179	1.43	30	0.008	57	0.91	-175
500	0.95	178	1.03	23	0.013	77	0.93	-179
600	0.95	173	0.76	14	0.019	78	0.95	176
700	0.95	170	0.56	7	0.023	75	0.96	173
800	0.96	166	0.39	5	0.025	76	0.97	169
900	0.97	163	0.33	9	0.032	84	0.97	166
1000	0.98	158	0.3	7	0.041	78	0.97	162

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D2218UK **OPTIMUM SOURCE AND LOAD IMPEDANCE**

Frequency	Z _S	ZL		
MHz	Ω	Ω		
500MHz	1.4 + j1.1	2.4 – j0.4		

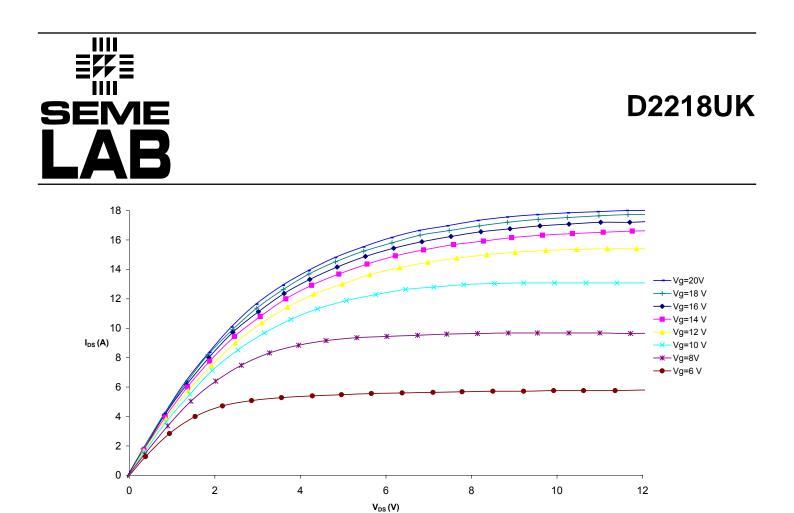
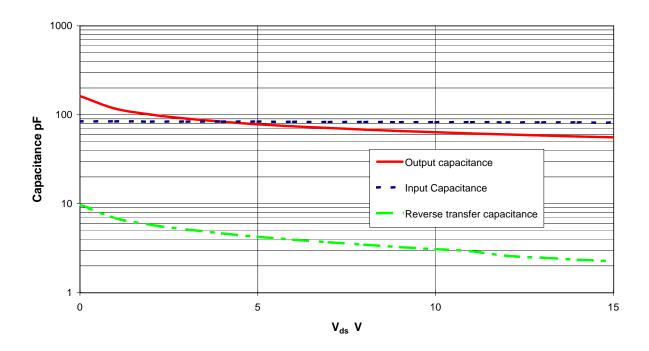


Figure 4 – Typical IV Characteristics.



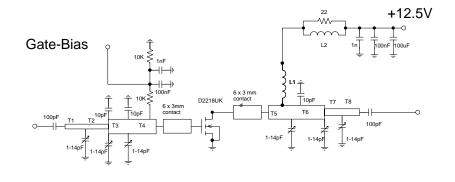


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D2218UK 500MHz TEST FIXTURE

Substrate Taconic RF35 0.8mm, Er=3.5

- T1 1.68mm wide, 21mm long
- T2 1.68mm wide, 104mm long
- T3 8.92mm wide, 17mm long
- T4 8.92mm wide, 13.5mm long
- T5 6.34mm wide, 11.5mm long
- T6 6.34mm wide, 9mm long
- T7 1.68mm wide, 13mm long
- T8 1.68mm wide, 28mm long
- L1 10 turns 0.5mm dia enamelled copper wire, 3mm i.d.
- L2 1.5 turns 0.5mm dia enamelled copper wire on Siemens B62152-A7X ferrite core

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